Silicon NPN Power Transistors 2SC2239

DESCRIPTION

·With TO-66 package
·Complement to type 2SA969
·High breakdown votage

APPLICATIONS

·Power amplifier applications
·Driver stage amplifier applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	160	V
V_{CEO}	Collector-emitter voltage	Open base	160	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
I_E	Emitter current		-1.5	A
P_T	Total power dissipation	T_C=25□	25	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA; I_B=0	160			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA; I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=500A; I_B=50mA			1.5	V
V_{BE}	Base-emitter on voltage	I_C=500mA ; V_{CE}=5V			1.0	V
I_{CBO}	Collector cut-off current	V_{CB}=160V ;I_E=0			1.0	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			1.0	μA
h_{FE}	DC current gain	I_C=100mA ; V_{CE}=5V	70		240	
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=10V,f=1MHz		25		pF
f_T	Transition frequency	I_C=100mA ; V_{CE}=10V		100		MHz

◆ **h_{FE} Classifications**

O	Y
70-140	120-240

PACKAGE OUTLINE

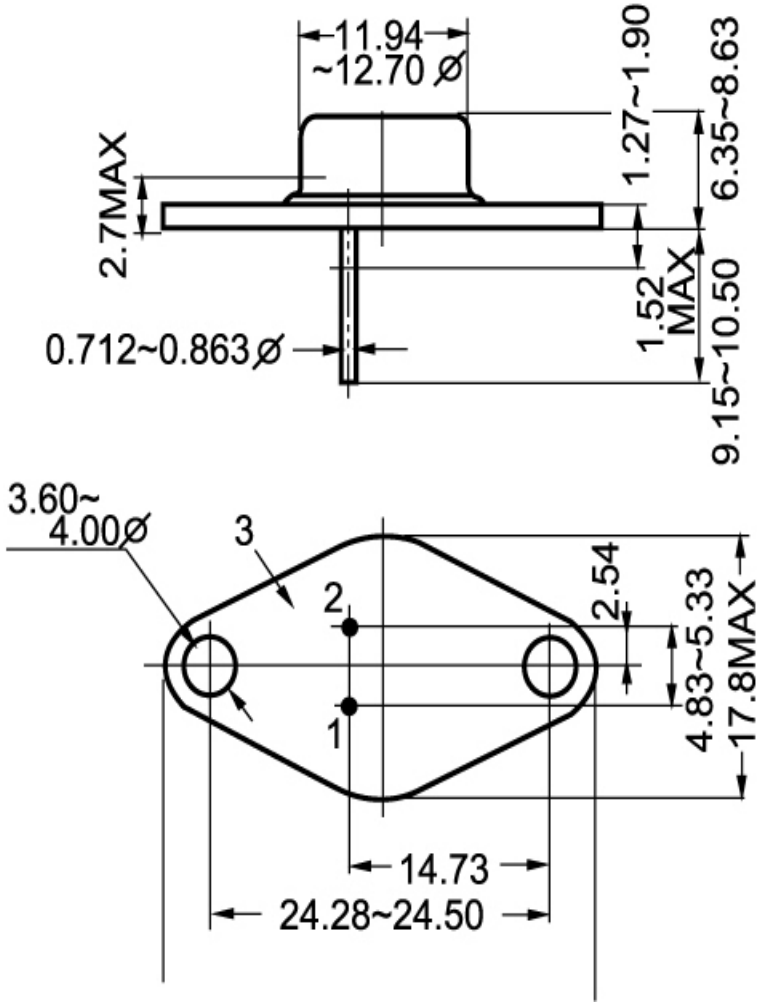

Fig.2 Outline dimensions